UNITED STATES PATENT AND TRADEMARK OFFICE

BEFORE THE PATENT TRIAL AND APPEAL BOARD

INNOSCIENCE AMERICA, INC.,
PETITIONER,

V.

INFINEON TECHNOLOGIES AUSTRIA AG,
PATENT OWNER.

Case No. IPR2025-00175
U.S. Patent 8,686,562

PETITIONER'S UPDATED EXHIBIT LIST

Further to 37 C.F.R. § 42.63(e), Petitioner hereby submits a current listing of its exhibits to counsel for Patent Owner. Exhibit 1037 was filed on P-TACTS and served via email to counsel of record for the Patent Owner.

Exhibits	Description
Ex-1001	U.S. Patent No. 8,686,562 ("the '562 patent")
Ex-1002	Expert Declaration of Dr. Yuji Zhao ("Zhao")
Ex-1003	Curriculum Vitae of Dr. Yuji Zhao
Ex-1004	U.S. Patent No. 5,943,601 to Usui et al. ("Usui")
Ex-1005	U.S. Patent Publication No. 2010/0052066 to Yu et al. ("Yu")
Ex-1006	U.S. Patent Publication No. 2008/0023726 to Adesida et al. ("Adesida")
Ex-1007	U.S. Patent No. 7,777,252 to Sugimoto et al. ("Sugimoto")
Ex-1008	Pearton et al., *Gallium Nitride Processing for Electronics, Sensors and Spintronics*, Springer, 10.1007/1-84628-359-0. (2006)
Ex-1009	Adachi, *Properties of Group-IV, III–V and II–VI Semiconductors*, John Wiley & Sons, Ltd, 10.1002/0470090340 (2005)
Ex-1010	U.S. Patent Publication No. 2007/0164321 to Sheppard et al. ("Sheppard")
Ex-1011	Mishra et al., *Semiconductor Device Physics and Design*, Springer (2008)
Ex-1012	Wu et al., *Very-High Power Density AlGaN/GaN HEMTs*, IEEE Transactions on Electronic Devices, Vol. 48, No. 3, March 2001
Ex-1013	Quay, *Gallium Nitride Electronics*, Springer, 10.1007/978-3-540-71892-5. (2008)

Exhibits	Description
Ex-1014	Mishra et al., *AlGaN/GaN HEMTs—An Overview of Device Operation and Applications*, Proceedings of the IEEE, Vol. 90, No. 6, June 2002
Ex-1015	Neaman, *Semiconductor Physics and Devices*, 3rd edition (2002)
Ex-1016	Voss, *Thermally Stable Ohmic and Schottky Contacts to GaN*, University of Florida, 2008
Ex-1017	Krämer, *Fabrication and characterization of metal-semiconductor contacts for application in AlxGa1-xN/GaN HEMTs*, (Oct. 31, 2000)
Ex-1018	Kuzmik et al., *Technology and Performance of InAlN/AlN/GaN HEMTs With Gate Insulation and Current Collapse Suppression Using ZrO_2 or HfO_2*, IEEE TRANSACTIONS ON ELECTRON DEVICES, Vol. 55, No. 3, Mar. 2008
Ex-1019	Wu et al., *Aluminum, magnesium, and gold contacts to contamination free n-GaN surfaces*, Journal of Applied Physics, Vol. 89, No. 1, Jan. 1, 2001
Ex-1020	Foresi et al., *Metal contacts to gallium nitride*, Appl. Phys. Lett., Vol. 62, No. 22, May. 31, 1993
Ex-1021	Kayali et al., *GaAs MMIC Reliability Assurance Guideline for Space Applications*, JPL Publication 96-25, Dec. 15, 1996
Ex-1022	U.S. Patent Publication No. 2009/0250816 to Chin et al. ("Chin")
Ex-1023	U.S. Patent No. 7,335,590 to Suh et al. ("Suh")
Ex-1024	U.S. Patent No. 6,607,976 to Chen et al. ("Chen")
Ex-1025	Excerpts from Bauccio, Michael, *Refractory Metals*, ASM Metals Reference Book, ASM International, American Society for Metals, ISBN 978-0-87170-478-8, (1993)
Ex-1026	Preuss, *Finer Copper Wires Make for Faster Integrated Circuits*, Berkeley Lab, https://www2.lbl.gov/Science-Articles/Archive/integrated-circuits-copper.html, Apr. 5, 1999

Exhibits	Description
Ex-1027	Cockeram, *The Diffusion Bonding of Silicon Carbide and Boron Carbide Using Refractory Metals*, USDOE Contract No. DE-AC1 1-98PN38206, Nov. 22, 1999
Ex-1028	Kim, *Atomic Layer Deposition of Metal and Nitride Thin films: Current Research Efforts and Applications for Semiconductor Device Processing*, RC22737 (W0303-012), Mar. 5, 2003
Ex-1029	U.S. Patent No. 6,844,258 to Fair et al. ("Fair")
Ex-1030	U.S. Patent No. 4,980,752 to Jones, Jr. ("Jones")
Ex-1031	U.S. Patent No. 5,635,763 to Inoue et al. ("Inoue")
Ex-1032	U.S. Patent No. 6,646,352 to Ohmi et al. ("Ohmi")
Ex-1033	Order Staying and Conditionally Closing Case, *Infineon Tech. Austria AG v. Innoscience (Suzhou) Tech. Company, Ltd.*, No. 4:24-cv-01553 (N.D. Ca. Aug. 30, 2024), ECF No. 56
Ex-1034	Excerpts from Prosecution History of the '562 Patent
Ex-1035	Excerpts from Rooy, E.L., *Introduction to Aluminum and Aluminum Alloys*, Metals Handbook, 10th Edition, Volume 2 Properties and Selection: Nonferrous Alloys and Special-Purpose Materials, ASM International, ISBN 978-0-87170-378-1, (October 1990)
Ex-1036	Pierson, Hugh O., *The Refractory Nitrides*, Handbook of Refractory Carbides and Nitrides, Properties, Characteristics, Processing and Applications, ISBN 978-0-8155-1392-6, (1996)
Ex-1037	Construing Certain Claim Terms, *Certain Semiconductor Devices and Products Containing the Same*, Inv. No. 337-TA-1414, Order No. 29 (Apr. 4, 2025)

Dated: April 23, 2025

By: /Lionel M. Lavenue/
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CERTIFICATE OF SERVICE

The undersigned hereby certifies that the foregoing **Petitioner's Updated Exhibit List and Exhibit 1037** were served on April 23, 2025, via email directed to counsel of record for the Patent Owner at the following:

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